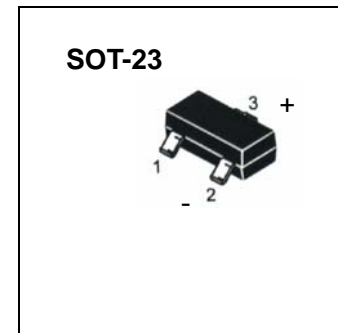
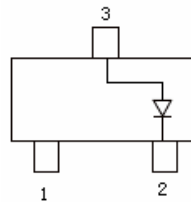


**BAL99** SWITCHING DIODE**FEATURES**

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

**Maximum Ratings @T_A=25°C**

Parameter	Symbol	Value	Unit
Non-Repetitive Peak reverse voltage DC Blocking Voltage	V_{RM} V_R	70	V
Average Rectified Output Current	I_O	100	mA
Power Dissipation	P_D	225	mW
Thermal Resistance. Junction to Ambient Air	$R_{\theta JA}$	556	°C/W
Junction temperature	T_J	150	°C
Storage temperature range	T_{STG}	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 100\mu A$	70		V
Reverse voltage leakage current	I_R	$V_R = 70V$		2.5	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		0.715 0.855 1 1.25	V
Diode Capacitance	C_D	$V_R = 0, f = 1MHz$		1.5	pF
Reveres recovery time	t_{rr}	$I_F = I_R = 10mA, R_L = 100\Omega,$ $I_{rr} = 0.1 \times I_R$		6	nS

Typical Characteristics

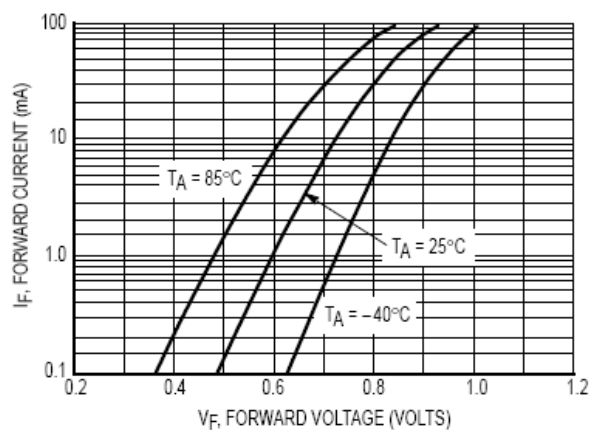


Figure 1. Forward Voltage

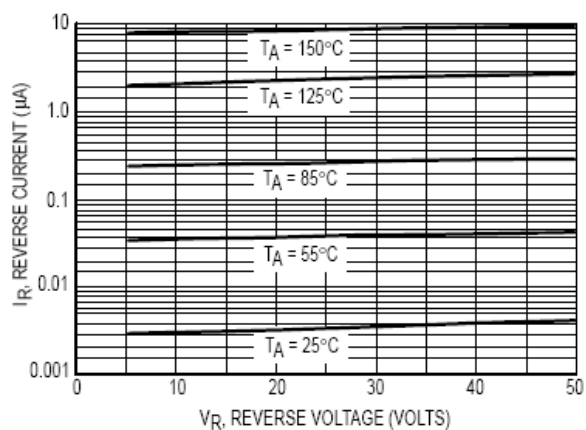


Figure 2. Leakage Current

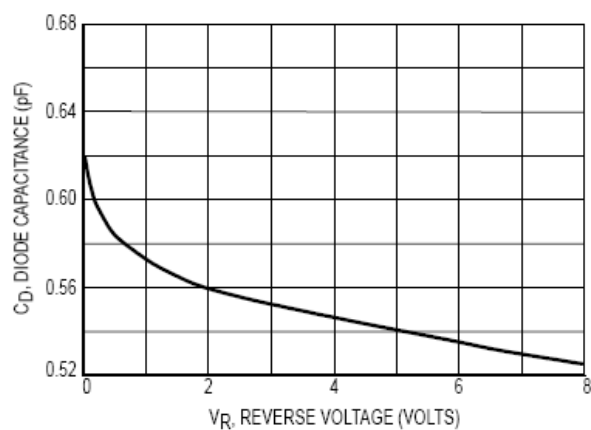


Figure 3. Capacitance